

Practice, Learn and Achieve Your Goal with Prepp UGC NET Exam

Electronic Science

Simplifying Government Exams



PAPER-II ELECTRONIC SCIENCE

Signature and	l Name	of Invigilator
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1.	(Signature) OMR Sheet No. :									
	(Name)		(To be filled by the Candidate)							
2.	(Signature)	I	Roll No.							
	(Name)			(In fi	gures	as per	r admi	ission	card)	
		I	Roll No							
Ι				(In wo	ords)				
Tir	$ne: 1 \frac{1}{4} hours]$					[Ma	aximu	ım M	arks	: 100
Nu	Imber of Pages in this Booklet : 8		Nun	nber of	Ques	stions	s in th	is Bo	oklet	: 50
	Instructions for the Candidates			परीक्ष	गर्थियों र	के लिए	र निर्देश	Т		
1. 2. 3.	 Write your roll number in the space provided on the top of this page. This paper consists of fifty multiple-choice type of questions. At the commencement of examination, the question booklet will be given to you. In the first 5 minutes, you are requested to open the booklet and compulsorily examine it as below : (i) To have access to the Question Booklet, tear off the paper seal on the edge of this cover page. Do not accept a booklet without sticker-seal and do not accept an open booklet. (ii) Tally the number of pages and number of questions in the booklet with the information printed on the cover page. Faulty booklets due to pages/questions missing or duplicate or not in serial order or any other discrepancy should be got replaced immediately by a correct booklet from the invigilator within the period of 5 minutes. Afterwards, neither the Question Booklet will be given. 	1. 2. 3.	पहले पृष्ठ के ऊप इस प्रश्न-पत्र में प परीक्षा प्रारम्भ हो मिनट आपको प्र लिए दिये जायेंगे, (i) प्रश्न-पुस्ति सील को प स्वीकार न (ii) कवर पृष्ठ की संख्या पुस्तिका जि में न हों अ करें तथा उ प्रश्न-पुस्ति उसके बाद ही आपको	रर नियत र पचास बहु ने पर, प्रश् श्न-पुस्तिव जिसकी प का खोलने हाड़ लें । करें । करें । करें । मर्म पृष्ठ/प श्र्यात किस् उसी समय का ले लें न तो आ अतिरिक्त	स्थान पर वेकल्पी न-पुस्ति का खोल जाँच आ के लिए खुली हु वरे शानुर पड़न क प्रश्न क प्रश्न क प्रश्न क प्रश्न क प्रश्न क प भी प्र पकी प्रश्	अपना य प्रश्न का आप ने तथा पको अ र उसके ई या बि सार प्रश्- चैक क न हों या कार क गौटाकर दिया ज दिया ज	रोल न हैं । गको दे व उसकी विश्य क कवर पे बना स्टी न-पुस्ति दुबारा दुबारा ो त्रुटिपू उसके पको पा तायेगा	म्बर लि दी जायेग निम्नति रुरनी है क पर त क ये पूरे का के प का के प म आ गये प पुस्ति स्थान प म म म स्यान प	खिए । गी । पह नखित ज : नगी काग ल की पु पृष्ठ तथ रे हैं । हों या स् का स्वी पर दूस ट दिये ज जायेगी	ले पाँच नाँच के गज की रुस्तिका 1 प्रश्नों दोषपूर्ण नीरियल कार न री सही नायेंगे । और न
4.	(iii) Find and the relation is over, in order, the order value is should be entered on this Test Booklet. Each item has four alternative responses marked (A), (B), (C) and (D). You have to darken the oval as indicated below on the correct response against each item. Example: \overrightarrow{A} \overrightarrow{B} \overrightarrow{D} where (C) is the correct response.	4.	(III) इस जाय प अंकित कर प्रत्येक प्रश्न के लि हैं । आपको सही कि नीचे दिखाया उदाहरण :	दें । तए चार उत्त उत्तर के व गया है । (A) (nt विकल रीर्घवृत्त र B	रूप (A) ल्प (A) को पेन	, (B), (से भरक D	(C) तथ र काल	ग (D) गि ा करना	का पर देये गये है जैसा
5.	Your responses to the items are to be indicated in the Answer Sheet given inside the Paper I Booklet only. If you mark at any place other than in the ovals in the Answer Sheet, it will not be evaluated.	5.	जबकि (C) सही प्रश्नों के उत्तर केव करने हैं । यदि अ स्थान पर उत्तर चि	उत्तर है । त्रल प्रश्न प 1प उत्तर पः ग्रह्नांकित व	त्र I के अ त्रक पर f करते हैं,	भन्दर दि देये गये तो उसव	ये गये उ दीर्घवृत्त का मूल्यां	त्तर-पत्रव के अल iकन नर्ह	क पर ही 11वा किस ीं होगा 1	अंकित नी अन्य ।
6.	Read instructions given inside carefully.	6.	अन्दर दिये गये वि	नेदेशों को	ध्यानपूर्व	कि पढ़ें	I ,	~		~
7.	Rough Work is to be done in the end of this booklet.	7.	कच्चा काम (Ro	ough Wo	ork) इर	प्त पुस्ति	का के 3	अन्तिम '	पृष्ठ पर	करे ।
δ.	If you write your name or put any mark on any part of the test booklet, except for the space allotted for the relevant entries, which may disclose your identity, you will render yourself liable to disqualification.	8. 9.	याद आप उत्तर-प् आपकी पहचान परीक्षा के लिये उ आपको परीक्षा न	गुस्तका प हो सके, वि अयोग्य घोर् समाप्त होग्	र अपना कसी भी षित कर ने पर प्र	ानाम य भाग प दिये ज श्न-पुसि	॥ एसा व र दर्शाते गयेंगे । तेका ए	काइ भो ंया अंगि वं OM	ानशान केत कर IR उत्त	ाजससे ते हैं तो र-पत्रक
9.	You have to return the test question booklet and OMR Answer sheet to the invigilators at the end of the examination compulsorily and must not carry it with you outside the		निरीक्षक महोदय अपने साथ परीक्ष	को लौटान 11 भवन से	ा आवश बाहर न	यक है अ 1 लेकर	और परी जायें ।	क्षा समा	फ्ति के ब	वाद उसे
	Examination Hall.	10.	केवल नीले/काल	ने बाल प्व	ाईंट पेन	का ही	इस्तेमात	ल करें	I	
10.	Use only Blue/Black Ball point pen.	11.	किसी भी प्रकार	का संगण	गक (कै	लकुलेव	टर) या	लाग टे	बल अ	ादि का
11.	Use of any calculator or log table etc., is prohibited.		प्रयोग वर्जित है			, c.	<u>ب</u> ب			
12.	There is no negative marks for incorrect answers.	12.	गलत उत्तरों के वि	ालए कोई	अक क	ाट नही	जाएँगे	I		

D-88-10

P.T.O.

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Know More

ELECTRONIC SCIENCE Paper – II

Note : This paper contains fifty (50) objective type questions, each question carrying two (2) marks. Attempt all the questions.

- **1.** Which diode exhibits negative resistance characteristics ?
 - (A) Zener diode
 - (B) Tunnel diode
 - (C) Schottky diode
 - (D) p-n junction diode
- 2. The effective mass of an electron in a band with a given (E, K) relationship is given by

(A)
$$\frac{\hbar}{dE/dK}$$
 (B) $\frac{\hbar^2}{dE/dK}$
(C) $\frac{\hbar^2}{d^2E/dK^2}$ (D) $\frac{\hbar}{d^2E/dK^2}$

- **3.** Transient response occurs in
 - (A) resistive circuit
 - (B) reactive circuit
 - (C) steady state
 - (D) open circuit
- 4. Superposition theorem is not valid for
 - (A) Voltage responses
 - (B) Current responses
 - (C) Power responses
 - (D) Phase responses
- 5. A field effect transistor is a
 - (A) current controlled device
 - (B) voltage controlled device
 - (C) gain controlled device
 - (D) drain controlled device
- 6. A differential amplifier is invariably in the input stage of all Op-Amps. This is done basically to provide the Op-Amps with a very high
 - (A) CMRR
 - (B) bandwidth
 - (C) slew rate
 - (D) open-loop gain

Paper-II

- 7. In a JK flip-flop the output state will toggle only when
 (A) J = 1, K = 0 (B) J = 0, K = 1
 (C) J = 0, K = 0 (D) J = 1, K = 1
- 8. D to A converter is achieved by
 - (A) ladder network
 - (B) dual-slope conversion
 - (C) astable multivibrator
 - (D) voltage controlled oscillator
- 9. Which interrupt has highest priority in 8085 ?
 - (A) RST 7.5 (B) RST 6.5
 - (C) RST 5.5 (D) TRAP
- **10.** A 4-bit data size is called
 - (A) data bus (B) baud
 - (C) byte (D) nibble
- **11.** The storage medium for the static storage class is
 - (A) CPU register
 - (B) memory
 - (C) accumulator
 - (D) stack
- 12. In C, executable program is created by
 - (A) compiler only
 - (B) linker only
 - (C) compiler and linker
 - (D) editor
- **13.** The cut off frequency for TEM wave is
 - (A) infinity
 - (B) zero

(C) 0

- (C) arbitrary frequency
- (D) that of TE_{10}

14. Depth of penetration of electromagnetic wave in free space is

(A) infinity (B)

(D) α (D) α

1

D-88-10

- **15.** Which of the following communication modes support two-way traffic but in only one direction at a time ?
 - (A) Simplex
 - (B) Half-duplex
 - (C) Three-quarter duplex
 - (D) Full-duplex
- 16. Intermediate frequency is used in
 - (A) AM transmitter
 - (B) FM transmitter
 - (C) Super heterodyne receiver
 - (D) Frequency division multiplexing
- **17.** Relaxation oscillator is made using
 - (A) SCR (B) FET
 - (C) UJT (D) BJT
- **18.** Which can measure pressure directly ?
 - (A) Thermistor
 - (B) Bourdon tube
 - (C) LVDT
 - (D) Strain gauge
- **19.** Bandwidth offered by optical fiber communication is of the order of
 - (A) 40 THz (B) 40 GHz
 - (C) 40 MHz (D) 10^{10} Hz
- **20.** In feed-back control system, overdamped condition for damping ratio will be equal to
 - (A) one
 - (B) greater than one
 - (C) less than one
 - (D) zero

Directions : Q. Nos. **21** to **30 : Assertion** & Reasoning type.

The following questions consist of two statements : one labelled as "Assertion (A)" and the other labelled as "Reason (R)". You are to examine these two statements carefully and decide if the Assertion (A) and the Reason (R) are individually true and if so, whether the

D-88-10

Reason is a correct explanation of the Assertion. Select your answers to these items using the codes given below and mark your answer accordingly.

Codes :

- (A) Both (A) and (R) are true and(R) is the correct explanation of (A).
- (B) Both (A) and (R) are true, but(R) is not the correct explanation of (A).
- (C) (A) is true, but (R) is false.
- (D) (A) is false, but (R) is true.
- 21. Assertion (A) : At room temperature, the Fermi level in a p-type semiconductor lies above the valance band, whereas that in the n-type semiconductor lies below the conduction band.
 - **Reason (R)** : At room temperature, the p-type semiconductor is rich in holes whereas the n-type semiconductor is rich in electrons.
- 22. Assertion (A): Thevenin's theorem is normally used to find the equivalent voltage source and Thevenin's equivalent resistance of a complex network.
 - **Reason (R)** : Thevenin theorem holds good for d.c. voltages but not for a.c. voltages.
- **23.** Assertion (A) : In the normal operation of BJT the emitter diode and collector diode are forward biased.
 - **Reason (R)** : In the active region the BJT can provide class-A operation.
- 24. Assertion (A) : R–2R ladder type D/A converter has a higher speed of conversion than a weighted resistance D/A converter.
 - **Reason (R)** : R–2R ladder type D/A converter uses a smaller number of passive components than the weighted resistance D/A converter.

Paper-II

- **25.** Assertion (A) : In Intel 8085, the lower type of address and data are multiplexed.
 - **Reason (R)** : This helps limit the number of external pin terminals.
- **26.** Assertion (A) : User defined functions are available as library functions in C compiler.
 - **Reason (R) :** User defined functions help to avoid repetition of same group of statements.
- 27. Assertion (A) : Helical antenna can be used as feeder for large parabolic reflectors to obtain circular polarization.
 - **Reason (R)** : Parabolic reflectors reverse the sense of polarization of the wave during reflection.
- 28. Assertion (A): In Hall effect, the open circuit transverse voltage developed by a current carrying semiconductor with a steady magnetic field imposed perpendicular to the current direction has opposite signs of ntype and p-type semiconductors.
 - **Reason (R) :** The magnetic field pushes both the holes and the electrons in the same direction.
- **29.** Assertion (A) : Optical fiber have broader bandwidth compared to conventional copper cables.
 - **Reason (R) :** The information carrying capacity of optical fibers is limited by dispersion and non-linear effects.
- **30.** Assertion (A) : Routh-Hurwitz criterion deals with stability of the system.
 - **Reason (R)** : Change of sign in the first column of Routh array suggests stability of the system.

31. Consider the devices.

2.	MOSFET
4.	CMOS
ence in	n which the
lecrease	es is
(B)	3, 1, 4, 2
(D)	1, 4, 2, 3
	2. 4. ence in lecrease (B) (D)

- **32.** Consider the following steps :
 - 1. Etching
 - 2. Exposure of ultra violet radiation
 - 3. Stripping
 - 4. Developing

After a wafer has been coated with photoresist, the correct sequence of these steps in photolithography is

- (A) 2, 4, 3, 1 (B) 2, 4, 1, 3 (C) 4, 2, 1, 3 (D) 3, 2, 4, 1
- **33.** Voltage regulator ICs are mentioned below

1.	7809	2.		7805	
3.	7815	4.		7812	
The	correct	sequence	in :	whicl	h the
outp	ut increa	ses is			
(A)	2, 1, 4,	3 (E	3)	1, 2, 3	, 4
(C)	3, 1, 4,	2 (I))	4, 3, 2	2, 1

- **34.** Consider the following communication systems :
 - 1. Telephony
 - 2. Radio communication
 - 3. Microwave communication
 - 4. Optical communication

The correct sequence of these systems from the point of view of increasing order of base band channels each one of them can accommodate is

- (A) 2, 4, 3, 1 (B) 3, 4, 1, 2 (C) 1, 2, 3, 4 (D) 4, 2, 1, 3
- (C) 1, 2, 3, 4 (D) 4, 2, 1, 3

35. Given below is a data size :

- 1. Byte 2. Nibble
- 3. Double Word 4. Word

The correct sequence in decreasing order of data size is

- (A) 1, 3, 4, 2 (B) 3, 4, 1, 2
- (C) 4, 2, 3, 1 (D) 2, 3, 4, 1

Paper-II

D-88-10

Direction : Q. Nos. 36 to 45 :

In the following question, match List–I with List–II and select the correct answer using the codes given below the lists :

36.	List – I	List – II	
	(a) BJT	(i) Trans-	
		conductance	
	(b) JFET	(ii) Breakdown	
		diodes	
	(c) Avalanche	(111) Photo masking	
	(d) IC	(iv) Emitter	
	fabrication	follower	
	Codes :	10110 WCI	
	(a) (b)	(c) (d)	
	(A) (iii) (ii)	(i) (iv)	
	(B) (iv) (i)	(ii) (iii)	
	(C) (i) (iv)	(iii) (ii)	
	(D) (ii) (iii)	(iv) (i)	
37	List – I	List – II	
011	(a) Laplace	(i) stability	
	(b) Poles and	(ii) current	
	zeros	source	
	(c) Norton's	(iii) short circuit	
	theorem		1
	(d) y-parameters	(iv) transient	
	Codos	analysis	
	(a) (b)	(c) (d)	
	(A) (i) (iii)	(iv) (ii)	
	(B) (iv) (i)	(ii) (iii)	
	(C) (ii) (iii)	(i) (iv)	
	(D) (iii) (ii)	(iv) (i)	
38	I ist _ I	I ist _ II	
50.	(a) Positive	(i) voltage	
	voltage	series	
	regulators		
	(b) JFET	(ii) 78 XX	
	(c) Feedback	(iii) Regenerative	
		feedback	
	(d) Multivibrator	(iv) Voltage	
		variable	
	Codos ·	resistor	
	(a) (b)	(c) (d)	
	(A) (i) (iii)	(ii) (iv)	
	(B) (ii) (iv)	(i) (iii)	
	(C) (iv) (iii)	(ii) (i)	
	(D) (iii) (iv)	(i) (ii)	
	(\mathbf{D}) (\mathbf{m}) (\mathbf{n})		

39.]	List –	- I		List – II
	(a) Fa	an out	t of 10	(i)	Mod-2 addition
	(b) X	OR		(ii)	Counter
	(c) D	ual sl	lope	(iii)) TTL
	(d) M	Iodul	ar-10	(iv)	A-D conversion
	Code	es:			
		(a)	(b)	(c)	(d)
	(A)	(i)	(ii)	(iv)	(iii)
	(B)	(ii)	(iii)	(i)	(iv)
	(C)	(iv)	(ii)	(iii)	(i)
	(D)	(iii)	(i)	(iv)	(ii)
40	L	ist _	T	T	ist _ II
TU.	(a) 8	13t 2085	1 (i	т 1	andshake
	(a) 0	005	(1) 11 m	anusnake
	(\mathbf{b}) 8	031	G	i) 2	key lockout
	(0) (0) (0) (0)	270	(i	1) 2- ii) SI	
	(d)	213	(1	\mathbf{v}	
	(\mathbf{u}) o	233	(1	v) U	-KDKUWI
	Coue	(2)	(\mathbf{b})	(c)	(d)
	(Λ)	(a)	(U) (ii)	(\mathbf{U})	(u) (iiii)
	(\mathbf{A})	(1) (ii)	(\mathbf{n})	$(\mathbf{i}\mathbf{v})$	(iii)
	(\mathbf{D})	(iv)	(i)	(\mathbf{i})	$(\mathbf{i}\mathbf{v})$
	(\mathbf{C})	(iv)	(iv)	(i)	(\mathbf{i})
	(D)	(111)	(\mathbf{IV})	(11)	(1)
41.		List –	- I		List – II
	(a) %	6 x		(i)	Post
					increment
	(b) v	vhile	(1)	(ii)	character
	(c) <i>x</i>	++		(iii)) infinite loop
	(1) (1,		(iv)	hex
	(d) `				
	(d) · Code	es :			
	(d) · Code	es: (a)	(b)	(c)	(d)
	(d) • • • • • • • • • • • • • • • • • • •	- es: (a) (iv)	(b) (iii)	(c) (i)	(d) (ii)
	(d) · Code (A) (B)	es: (a) (iv) (iii)	(b) (iii) (ii)	(c) (i) (iv)	(d) (ii) (i)
	(d) . Code (A) (B) (C)	es: (a) (iv) (iii) (i)	(b) (iii) (ii) (iii)	(c) (i) (iv) (ii)	(d) (ii) (i) (iv)
	(d) · Code (A) (B) (C) (D)	es: (a) (iv) (iii) (i) (ii)	(b) (iii) (ii) (iii) (iv)	(c) (i) (iv) (ii) (i)	(d) (ii) (i) (iv) (iii)
42	(d) · Code (A) (B) (C) (D)	L (a) (iv) (iii) (i) (ii)	(b) (iii) (ii) (iii) (iv)	(c) (i) (iv) (ii) (i)	(d) (ii) (i) (iv) (iii) List – II
42.	(d) · Code (A) (B) (C) (D)	+ es: (a) (iv) (iii) (ii) (ii) List -	(b) (iii) (ii) (iii) (iv) - I	(c) (i) (iv) (ii) (i) (i)	(d) (ii) (i) (iv) (iii) List – II Pressure
42.	(d) · Code (A) (B) (C) (D) (a) C	- es: (a) (iv) (iii) (ii) (ii) List - bapaci	(b) (iii) (iii) (iii) (iv) - I tive	(c) (i) (iv) (ii) (i) (i)	(d) (ii) (i) (iv) (iii) List – II Pressure
42.	(d) · Code (A) (B) (C) (D) (a) C tr (b) T	(a) (iv) (iii) (i) (ii) List - bapaci ansdu	(b) (iii) (iii) (iii) (iv) - I tive	(c) (i) (iv) (ii) (i) (i)	(d) (ii) (i) (iv) (iii) List – II Pressure
42.	(d) · Code (A) (B) (C) (D) (a) C tr (b) T (c) L	es: (a) (iv) (iii) (ii) List - bapaci ansdu hermo	(b) (iii) (ii) (iv) - I tive acer xcouple	(c) (i) (iv) (ii) (i) (i) (i) e (ii)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement
42.	(d) · Code (A) (B) (C) (D) (a) C (b) T (c) L (d) D	(iv) (iv) (iii) (i) (ii) (ii) List - ansdu hermo oad c	(b) (iii) (iii) (iv) - I tive accer pocoupled tell	(c) (i) (iv) (ii) (i) (i) (i) (ii) (iii) (iii)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement
42.	(d) · Code (A) (B) (C) (D) (a) C (b) T (c) L (d) D Code	(iv) (iv) (iii) (ii) (ii) List - apaci ansdu hermo oad c	(b) (iii) (iii) (iv) - I tive accer accoupled reagm	(c) (i) (iv) (ii) (i) (i) (i) (i) (ii) (iv)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature
42.	(d) . (A) (B) (C) (D) (a) C tr (b) T (c) L (d) D Code	es: (a) (iv) (iii) (ii) (ii) List - bapaci ansdu hermo oad c biaphn es: (a)	(b) (iii) (iii) (iv) - I tive acer xcouple regul ragm	(c) (i) (iv) (ii) (i) (i) (i) (ii) (iii) (iv)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature
42.	(d) · Code (A) (B) (C) (D) (a) C (b) T (c) L (d) D Code (A)	es: (a) (iv) (iii) (i) (ii) List - bapaci ansdu hermo oad c oiaphn es: (a) (ii)	(b) (iii) (iii) (iv) - I tive accer occoupled reall ragm (b) (iv)	(c) (i) (iv) (ii) (i) (i) (i) (ii) (iii) (iv) (c) (iii)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature (d) (i)
42.	(d) . Code (A) (B) (C) (D) (a) C tr (b) T (c) L (d) D Code (A) (C) (C) (C) (C) (D) (C) (C) (C) (C) (C) (C) (C) (C	$\begin{array}{c} -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ -\\ $	(b) (iii) (iii) (iv) - I tive icer occupte cell ragm (b) (iv) (i)	(c) (i) (iv) (ii) (i) (i) (i) (ii) (iii) (iv) (c) (iii) (iii) (iii)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature (d) (i) (iv)
42.	(d) • Code (A) (B) (C) (D) (a) C (c) L (d) D Code (A) (B) (C)	$\begin{array}{c} + \\ + \\ + \\ + \\ + \\ + \\ + \\ + \\ + \\ + $	(b) (iii) (iii) (iv) - I tive cer xcouple rell ragm (b) (iv) (i) (i)	(c) (i) (iv) (ii) (i) (i) (ii) (iii) (iv) (c) (iii) (ii) (iii)	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature (d) (i) (iv) (iv)
42.	(d) · Code (A) (B) (C) (D) (a) C (b) T (c) L (d) D Code (A) (B) (C) (D)	$\begin{array}{c} -\\ \mathbf{es:}\\ (a)\\ (iv)\\ (iii)\\ (ii)\\ (ii)\\ \mathbf{List} -\\ \mathbf{capaci}\\ capac$	(b) (iii) (iii) (iv) - I tive cer couple reall ragm (b) (iv) (i) (i) (jv)	(c) (i) (iv) (ii) (i) (i) (i) (ii) (ii) (i	(d) (ii) (i) (iv) (iii) List – II Pressure Strain Displacement Temperature (d) (i) (iv) (iv) (iv)

D-88-10

Paper-II

5

Know More

43.		List – I		List – II
	(a)	Frequency	(i)	Envelop
	(b)	Modulation		detection
	(D)	suppressed	e (11)	Companding
		carrier		
	(c)	PCM	(iii)	Balanced
	(1)		<i>(</i> •)	modulator
	(d)	Amplitude	(1V)	Pre-
		modulation		and de-
				emphasis
	Co	des :		
		(a) (b)	(c)	(d)
	(A)	(1) $(11)(i)$ (ii)	(111) (iv)	(1V) (iii)
	(\mathbf{D})	(1) $(11)(12)$ (11)	$(\mathbf{i}\mathbf{v})$	(iii)
	(D)	(iv) (iii)	(ii)	(i)
	~ /		. ,	
44.		List – I	$\langle \cdot \rangle$	List – II
	(a)	LASER	(1)	Emits light of
	(b)	Solar cell	(ii)	Consumes
	(0)		(11)	electrical power
				due to the
				incident light
	(c)	Photo diode	(iii)	Delivers
	(d)	LED	(iv)	Finite bigh
	(u)	LLD	(1)	energy
				coherent beam
	Co	des :		
	(\mathbf{A})	(a) (b)	(c) (i)	(d)
	(\mathbf{A})	(1V) $(111)(iii)$ (iv)	(1) (ii)	(11) (i)
	(\mathbf{D})	(in) (iv) (iii)	(ii) (iii)	(i)
	(D)	(iii) (iv)	(i)	(ii)
45.		List – I	$\langle \cdot \rangle$	List – II
	(a)	Proportional	(1)	hysteresis
	(b)	On-off	(ii)	stability
	(0)	control	(11)	state may
	(c)	Bode plot	(iii)	variable gain
	(1)		$\langle \cdot \rangle$	amplifier
	(d)	Routh-	(1V)	frequency
	Co	des :		response
	0.0	(a) (b)	(c)	(d)
	(A)	(iii) (i)	(iv)	(ii)
	(B)	(i) (ii)	(iv)	(iii)
	(\mathbf{C})	(ii) (i)	(iii)	(iv)
	(D)	(1V) (111)	(1)	(11)

Read the paragraph and answer the questions 46 to 50.

Power devices with pnpn layers such as SCR, SCS and GTO belong to thyristor series. However, UJT is also a member of this group. The most popular pnpn device - the SCR was introduced in 1956 bv Bell Telephone Laboratories. It has capability to control power as high as 10 MW with individual ratings upto 2000 A at 1800 V. The frequency range of its application has also been extended upto 50 KHz hence it is used in induction heating and ultrasonic cleaning.

A simple p-n junction diode is a rectifier without control action. SCR is a rectifier with control action. The third element called gate enables the controlled rectification gate is used to turn the SCR on but not to turn it off. In the off state the resistance of SCR is large upto 100 K Ω while in the on state its dynamic resistance is typically 0.01 to 0.1 Ω . As it has to handle high power and high temperature, SCR is made of Si.

To turn the SCR on a positive pulse of suitable amplitude must be applied to the gate terminal when the anode is positive with respect to the cathode. However, removal of gate signal does not turn the SCR off. The general methods used for turning the SCR off are (i) anode current interruption and (ii) forced commutation. It is not recommended to turn the SCR on with zero gate signal.

The specifications of SCR given in the data sheet include forward breakover voltage, latching current, holding current, reverse break-down voltage, turn-on time, turn-off time, gate ratings and junction temperature T_i .

Paper-II

D-88-10

Some of the applications of SCR are controls, relay controls, motor inverters, cycloconverters, preventive circuits, regulated power supplies and phase control. Another pnpn device having characteristic similar to that of SCR is SCS - silicon controlled switch. However it has two gate terminals. The additional gate at the anode side can be used to turn SCS off. The turn off time of SCS is 1 to 10 µs as against 5 to 30 us for that of SCR. Other advantages of SCS over SCR are

- 1. increased control
- 2. triggering sensitivity and
- 3. more predictable firing

At present SCS is limited to low power current and voltage ratings. It can dissipate 100 to 500 mW power. Some of the applications of SCS are pulse generation, voltage sensing and oscillators.

Gate turn off (GTO) switch is one more pnpn device which can be turned on or off with cathode gate. The gate current requirement of GTO is greater than that for SCR but its turn off time (1 μ s) is much smaller than that for SCR. This makes GTO a faster device. Some of the applications of GTO are counters, pulse generators, multivibrators and voltage regulators.

Light activated SCR is turned on by the light falling on the gate. It is used as a relay, optical light controller, phase controller and motor control device. An interesting application of LASCR is in AND and OR circuits.

One more pnpn device is Shockley diode which can be used as trigger

switch for SCR like UJT. A diac is also used for triggering and it provides triggering in either direction.

A device that can control ac power to the load during the positive and negative cycles of input is called triac. It is basically a diac with a gate terminal for bilateral turn on.

- **46.** In the ON state the voltage drop across the SCR is approximately equal to
 - (A) Anode voltage
 - (B) Cathode voltage
 - (C) 1 to 1.5 V
 - (D) Gate voltage

47. For complete isolation between load and signal which device is preferred ?

(A) Diac(B) LASCR(C) SCR(D) Triac

48. Which device is useful for high frequency application ?

- (A) SCS (B) GTO (C) Triac (D) SCP
- (C) Triac (D) SCR
- **49.** There is a danger of $\frac{di}{dt}$ failure of SCR if it is triggered with _____ gate current.
 - (A) positive
 - (B) negative
 - (C) zero
 - (D) sinusoidal

50. Forced commutation is employed when anode voltage is

- (A) dc
- (B) ac
- (C) pulsating
- (D) triangular

D-88-10

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